



## **GA20SICP12-247 Information**



For Reference Only

Part Number GA20SICP12-247

Manufacturer GeneSiC Semiconductor

**Category** Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** TRANS SJT 1200V 45A TO247

Package TO-247-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **Certified Quality**

Heisener's commitment to quality has shaped our processes for sourcing, testing, shipping, and every step in between. This foundation underlies each component we sell.









## **GA20SICP12-247 Specifications**

Manufacturer Part Number         GA20SICP12-247           Manufacturer         GeneSiC Semiconductor           Category         Discrete Semiconductor Products           Transistors - FETs, MOSFETs - Single           Package         TO-247-3           Series         -           FET Type         -           Technology         SiC (Silicon Carbide Junction Transistor)           Drain to Source Voltage (Vdss)         1200V           Current - Continuous Drain (Id) @ 25°C         45A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         -           Vgs(th) (Max) @ Id         -           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         3091pF @ 800V           Vgs (Max)         Vg           Vgs (Max)         2           Pett Feature         -           Power Dissipation (Max)         282W (Tc)           Rds On (Max) @ Id, Vgs         50 mOhm @ 20A           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247AB           Package / Case         TO-247-3		
CategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-247-3Series-FET Type-TechnologySiC (Silicon Carbide Junction Transistor)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C45A (Tc)Drive Voltage (Max Rds On, Min Rds On)-Vgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds3091pF @ 800VVgs (Max)-FET Feature-Power Dissipation (Max)282W (Tc)Rds On (Max) @ Id, Vgs50 mOhm @ 20AOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ABPackage / CaseTO-247-3	Manufacturer Part Number	GA20SICP12-247
Package         TO-247-3           Series         -           FET Type         -           Technology         SiC (Silicon Carbide Junction Transistor)           Drain to Source Voltage (Vdss)         1200V           Current - Continuous Drain (Id) @ 25°C         45A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         -           Vgs(th) (Max) @ Id         -           Gate Charge (Qg) (Max) @ Vgs         -           Input Capacitance (Ciss) (Max) @ Vds         3091pF @ 800V           Vgs (Max)         -           FET Feature         -           Power Dissipation (Max)         282W (Tc)           Rds On (Max) @ Id, Vgs         50 mOhm @ 20A           Operating Temperature         -55°C ~ 175°C (TJ)           Mounting Type         Through Hole           Supplier Device Package         TO-247AB           Package / Case         TO-247-3	Manufacturer	GeneSiC Semiconductor
PackageTO-247-3Series-FET Type-TechnologySiC (Silicon Carbide Junction Transistor)Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C45A (Tc)Drive Voltage (Max Rds On, Min Rds On)-Vgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds3091pF @ 800VVgs (Max)-FET Feature-Power Dissipation (Max)282W (Tc)Rds On (Max) @ Id, Vgs50 mOhm @ 20AOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ABPackage / CaseTO-247-3	Category	Discrete Semiconductor Products
Series - General Sic (Silicon Carbide Junction Transistor)  FET Type - SiC (Silicon Carbide Junction Transistor)  Drain to Source Voltage (Vdss) 1200V  Current - Continuous Drain (Id) @ 25°C 45A (Tc)  Drive Voltage (Max Rds On, Min Rds On) - Vgs(th) (Max) @ Id - Gate Charge (Qg) (Max) @ Vgs - Gate Charge (Qg) (Max) @ Vds 3091pF @ 800V  Vgs (Max) - FET Feature - Power Dissipation (Max) 282W (Tc)  Rds On (Max) @ Id, Vgs 50 mOhm @ 20A  Operating Temperature - 55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-247AB  Package / Case To source (Sis (Carbide Junction Transistor)  SiC (Silicon Carbide Jun		Transistors - FETs, MOSFETs - Single
FET Type  Technology  SiC (Silicon Carbide Junction Transistor)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  45A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  - Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  - FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Supplier Device Package  TO-247AB  Package / Case	Package	TO-247-3
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  45A (Tc)  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  Vgs (Max)  - FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Supplier Device Package  Package / Case  SiC (Silicon Carbide Junction Transistor)  1200V  45A (Tc)  45A (Tc)	Series	-
Drain to Source Voltage (Vdss)1200VCurrent - Continuous Drain (Id) @ 25°C45A (Tc)Drive Voltage (Max Rds On, Min Rds On)-Vgs(th) (Max) @ Id-Gate Charge (Qg) (Max) @ Vgs-Input Capacitance (Ciss) (Max) @ Vds3091pF @ 800VVgs (Max)-FET Feature-Power Dissipation (Max)282W (Tc)Rds On (Max) @ Id, Vgs50 mOhm @ 20AOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ABPackage / CaseTO-247-3	FET Type	-
Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)	Technology	SiC (Silicon Carbide Junction Transistor)
Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  Package / Case  TO-247-3	Drain to Source Voltage (Vdss)	1200V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs - Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max) - FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole Supplier Device Package Package / Case  - Case - Ca	Current - Continuous Drain (Id) @ 25°C	45A (Tc)
Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)	Drive Voltage (Max Rds On, Min Rds On)	-
Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  - FET Feature  - Power Dissipation (Max)  Rds On (Max) @ Id, Vgs  50 mOhm @ 20A  Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247AB  Package / Case  TO-247-3	Vgs(th) (Max) @ Id	-
Vgs (Max)	Gate Charge (Qg) (Max) @ Vgs	-
FET Feature -  Power Dissipation (Max) 282W (Tc)  Rds On (Max) @ Id, Vgs 50 mOhm @ 20A  Operating Temperature -55°C ~ 175°C (TJ)  Mounting Type Through Hole  Supplier Device Package TO-247AB  Package / Case TO-247-3	Input Capacitance (Ciss) (Max) @ Vds	3091pF @ 800V
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Rds On (Max) @ Id, Vgs50 mOhm @ 20AOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-247ABPackage / CaseTO-247-3	FET Feature	-
Operating Temperature  -55°C ~ 175°C (TJ)  Mounting Type  Through Hole  Supplier Device Package  TO-247AB  Package / Case  TO-247-3	Power Dissipation (Max)	282W (Tc)
Mounting Type Through Hole Supplier Device Package TO-247AB Package / Case TO-247-3	Rds On (Max) @ Id, Vgs	50 mOhm @ 20A
Supplier Device Package TO-247AB Package / Case TO-247-3	Operating Temperature	-55°C ~ 175°C (TJ)
Package / Case TO-247-3	Mounting Type	Through Hole
	Supplier Device Package	TO-247AB
Report errors?	Package / Case	TO-247-3
		Report errors?

#### **GA20SICP12-247 Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

### **GA20SICP12-247 Payment Methods**



















### **GA20SICP12-247 Shipping Methods**













If you have any question about GA20SICP12-247, please do not hesitate to contact us!

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